ALPHA & OMEGA
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Alpha & Omega Semiconductor Product Reliability Qualification Report

AOGT68801Q rev B

ALPHA & OMEGA Semiconductor, Inc

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This report delineates the product's quality and reliability test outcomes. Specific sample sizes undergo accelerated environmental tests, with corresponding electrical testing before and after each interval. Analysis of the conclusive electrical test results affirms the product's adherence to AOS quality and reliability standards in accordance with **AEC-Q101-Rev-E**. Reference to the existing qualification outcomes for similar products is warranted due to structural similarities. The released product will be classified by its process family and undergo regular monitoring to ensure continual enhancements in product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Duration	Lots/SS	Number of Failures	Reference Standard
HTGB + *High Temperature Gate Bias*	**175°C** **Vgs=100% of Positive Vgsmax**	**1000 hrs**	**3 * 77**	**0/231**	**JESD22-A108**
HTGB - *High Temperature Gate Bias*	**175°C** **Vgs= 100% of Negative Vgsmax**	**1000 hrs**	**3 * 77**	**0/231**	**JESD22-A108**
HTRB *High Temperature Reverse Bias*	**175°C** **Vds=100% of Vdsmax**	**1000 hrs**	**3 * 77**	**0/231**	**JESD22-A108**
PC *Precondition*	**168 hrs, 85°C, 85%RH,** **3 cycles reflow @ 260°C** **(MSL 1)**	**-**	**15 * 77**	**0/1155**	**JESD22-A113** **J-STD-020**
HAST* *Highly Accelerated Stress Test*	**130°C, 85%RH,** **Vds = 80% of Vdsmax** **up to 42V**	**96 hrs**	**3 * 77**	**0/231**	**JESD22-A110**
H3TRB* *High Humidity High Temperature Reverse Bias*	**85°C, 85%RH,** **Vds = 80% of Vdsmax** **up to 100V**	**1000 hrs**	**3 * 77**	**0/231**	**JESD22-A101**
AC* *Autoclave*	**121°C, 100%RH, 15psig**	**96 hrs**	**3 * 77**	**0/231**	**JESD22-A102**
TC* *Temperature Cycling*	**-55°C to 150°C,** **air to air**	**1000 cycles**	**3 * 77**	**0/231**	**JESD22-A104**
IOL* *Intermittent Operational Life*	**ΔTj = 100°C** t_{on} **= 2 minutes** t_{off} **= 2 minutes**	**15000 cycles**	**3 * 77**	**0/231**	**MIL-STD-750** **Method 1037**
ESD_HBM	**Class H3A** **(>4000V to ⩽8000V)**	**-**	**30 pcs**	**-**	**AEC-Q101-001**
ESD_CDM	**Class C2b** **(750 to <1000 V)**	**-**	**30 pcs**	**-**	**AEC-Q101-005**
DPA *Destructive Physical Analysis*	**Random sample of parts that have successfully completed H3TRB**	**-**	**1 * 2**	**0/2**	**AEC-Q101-004**
DPA *Destructive Physical Analysis*	**Random sample of parts that have successfully completed HAST**	**-**	**1 * 2**	**0/2**	**AEC-Q101-004**
DPA *Destructive Physical Analysis*	**Random sample of parts that have successfully completed TC**	**-**	**1 * 2**	**0/2**	**AEC-Q101-004**
PV *Parametric Verification*	**Tj= -55°C ,25°C ,175°C**	**-**	**75 pcs**	**0/75**	**Datasheet**

Notes:
* For SMD devices reliability stress tests performed after PC (precondition).

II. Reliability Evaluation

FIT rate (per billion): 2.61
MTTF = 43670 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

At 60% Confidence Level
Failure Rate = $\text{Chi}^2 \times 10^9$ **/ [**2 (N) (H) (Af)**] =** 2.61
MTTF = 10^9 / FIT = 43670 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval
N = Total Number of units from burn-in tests
H = Duration of burn-in testing
Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and T_J u = 55°C)
Acceleration Factor [**Af**] = **Exp** [Ea / **k** (1/T_J u – 1/T_J s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	125 deg C	150 deg C	175 deg C
Af	**758**	**256**	**95**	**38**	**9.7**	**2.9**	**1**

T_J s = Stressed junction temperature in degree (Kelvin), K = C + 273.16
T_J u =The use junction temperature in degree (Kelvin), K = C + 273.16
k = Boltzmann’s constant, 8.617164 X 10^{-5}eV / K